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**BUX21**

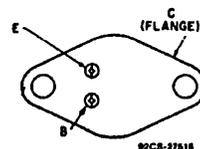
**Silicon N-P-N  
 Switching Transistor**

For Switching Applications In  
 Industrial and Commercial Equipment

**Features:**

- $V_{CE0} - 200V$
- $I_C - 40 A$
- $P_T - 250 W$

**TERMINAL DESIGNATIONS**



**JEDEC TO-204AA**

The BUX21 is a silicon NPN power transistor featuring fast switching speeds, low saturation voltage, and high safe-operation area (SOA) ratings. It is specially designed for converters, inverters, pulse-width-modulated regulators, and a variety of power switching circuits.

The BUX21 transistor is supplied in a steel JEDEC TO-204AA hermetic package.

**MAXIMUM RATINGS, Absolute-Maximum Values:**

	<b>BUX21</b>	
$V_{CB0}$ .....	250	V
$V_{CE0(SUS)}$ .....	200	V
$V_{CEX(SUS)}$ .....		
$V_{BE} = -1.5V$ .....	250	V
$V_{CER(SUS)}$ .....		
$R_{BE} = 100 \Omega$ .....	240	V
$V_{EBO}$ .....	7	V
$I_C$ .....	40	A
$I_{CM}$ .....	50	A'
$I_B$ .....	8	A
$P_T$ .....		
At $T_C$ up to $25^\circ C$ and $V_{CE}$ up to 20 V .....	250	W
$T_J, T_{sig}$ .....	-65 to +200	$^\circ C$
$T_L$ .....		
At distances $\geq 1/16$ in. (1.58 mm) from case for 10 s max. ....	200	$^\circ C$



**Quality Semi-Conductors**

ELECTRICAL CHARACTERISTICS, at Case Temperature ( $T_C$ ) = 25°C unless otherwise specified

CHARACTERISTIC	TEST CONDITIONS				LIMITS			UNITS
	VOLTAGE V dc		CURRENT A dc		BUX21			
	V <sub>CE</sub>	V <sub>BE</sub>	I <sub>C</sub>	I <sub>B</sub>	Min.	Typ.	Max.	
I <sub>CEO</sub>	160	—	—	0	—	—	3	mA
I <sub>CEV</sub>	250	-1.5	—	—	—	—	3	
T <sub>C</sub> = 125°C	250	-1.5	—	—	—	—	12	
I <sub>EBO</sub>	—	-5	0	—	—	—	1	
V <sub>CEO(sus)</sub> <sup>b</sup>	—	—	0.2 <sup>a</sup>	—	200 <sup>a</sup>	—	—	V
V <sub>(BR)EBO</sub> I <sub>E</sub> = 0.05 A	—	—	0	—	7	—	—	V
V <sub>BE(sat)</sub>	—	—	25 <sup>a</sup>	3	—	1.2	1.5	
V <sub>CE(sat)</sub>	—	—	12 <sup>a</sup> 25 <sup>a</sup>	1.2 3	—	0.2 0.7	0.6 1.5	
h <sub>FE</sub>	2 4	—	12 <sup>a</sup> 25 <sup>a</sup>	—	20 10	—	60 —	
I <sub>S/b</sub> t = 1s, nonrepetitive	140 20	—	—	—	0.15 12.5	—	—	A
f <sub>T</sub> f = 10 MHz	15	—	2	—	8	—	—	MHz
t <sub>on</sub>	V <sub>CC</sub> = 100 V	—	25	3	—	0.3	1.2	μs
t <sub>s</sub> (I <sub>B1</sub> = I <sub>B2</sub> )	V <sub>CC</sub> = 100 V	—	25	3	—	1.0	1.8	
t <sub>f</sub> (I <sub>B1</sub> = I <sub>B2</sub> )	V <sub>CC</sub> = 100 V	—	25	3	—	0.2	0.4	
R <sub>θJC</sub>	—	—	—	—	—	—	0.7	°C/W

<sup>a</sup> Pulsed, pulse duration = 300 μs, duty factor < 2%.

<sup>b</sup> CAUTION: Sustaining Voltages V<sub>CEO(sus)</sub> MUST NOT be measured on a curver tracer.

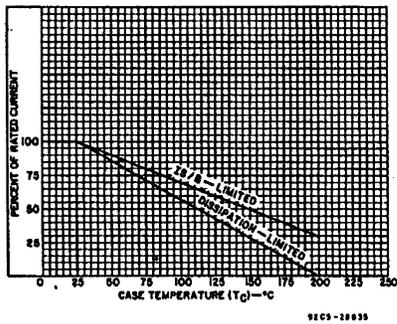


Fig. 1 — Dissipation and I<sub>S</sub> derating curve.

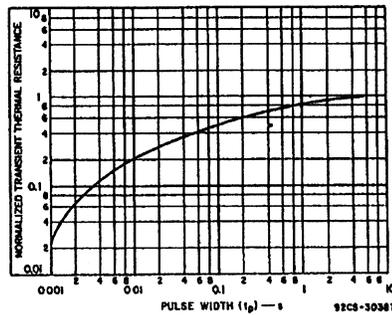


Fig. 2 — Typical thermal-response characteristic.